

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re patent application of

Tae-Hee CHOE, et al.

Serial No.

[Division of Serial No. 09/989,112, filed November 21, 2001]

Filed: November 17, 2003

For: SOI SUBSTRATE HAVING AN ETCH STOP LAYER, AND FABRICATION METHOD THEREOF,
SOI INTEGRATED CIRCUIT FABRICATED THEREON, AND METHOD OF FABRICATING
SOI INTEGRATED CIRCUIT USING THE SAME

CONFIRMATION
CLAIM FOR CONVENTION PRIORITY

Commissioner for Patents
Alexandria, VA 22313-1450

Sir:

The benefit of the filing date of the following prior foreign application filed in the following foreign country is hereby requested, and the right of priority provided in 35 U.S.C. §119 is hereby claimed:

Application No. 2001-28008 - filed May 22, 2001 - Republic of Korea

In support of this claim, a certified copy of said original foreign application was filed in parent application Serial No. 09/989,112 on November 21, 2001.

Acknowledgment of applicant's claim for priority and receipt of the certified priority document is solicited.

Respectfully submitted,

Date: November 17, 2003


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